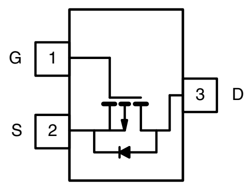
P-Channel 8 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
- 8	0.030 at V_{GS} = - 4.5 V	- 6[e]	11.8 nC
	0.036 at V_{GS} = - 2.5 V	- 6[e]	
	0.048 at V_{GS} = - 1.8 V	- 5.9	
	0.068 at V_{GS} = - 1.5 V	- 5	
	0.120 at V_{GS} = - 1.2 V	- 3.7	

TO-236
(SOT-23)



Top View

Si2329DS (D9)*

*** Marking Code**

Ordering Information: Si2329DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free

RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Load Switch
- Low Voltage Gate Drive
  - Low On-Resistance
- Battery Management in Portable Equipment

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 8	V
Gate-Source Voltage		V_{GS}	± 5	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 6[e]	A
	T_C = 70 °C		- 6	
	T_A = 25 °C		- 5.3[b, c]	
	T_A = 70 °C		- 4.2[b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	- 20	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 2.1	
	T_A = 25 °C		- 1.0[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.5	W
	T_C = 70 °C		1.6	
	T_A = 25 °C		1.25[b, c]	
	T_A = 70 °C		0.8[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	≤ 5 s	R_{thJA}	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

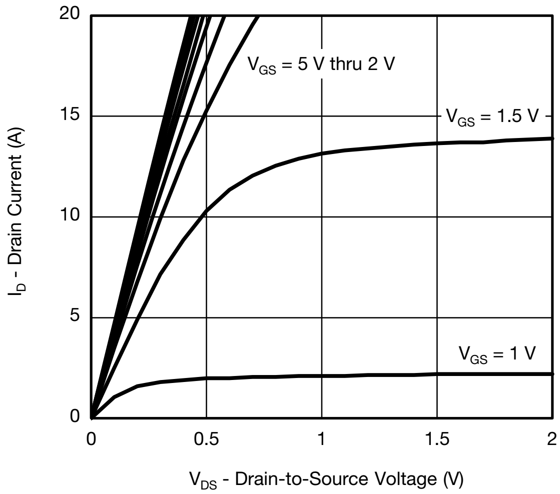
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 166 °C/W.
e. Package limited.

MOSFET SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 6		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250 µA	- 0.35		- 0.8	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 8 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 8 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ - 5 V, V_{GS} = - 5.3 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 5.3 A		0.025	0.030	Ω
		V_{GS} = - 2.5 V, I_D = - 4.8 A		0.030	0.036	
		V_{GS} = - 1.8 V, I_D = - 4.2 A		0.037	0.048	
		V_{GS} = - 1.5 V, I_D = - 3.5 A		0.045	0.068	
		V_{GS} = - 1.2 V, I_D = - 0.8 A		0.060	0.120	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 4 V, I_D = - 5.3 A		2.0		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 4 V, V_{GS} = 0 V, f = 1 MHz		1485		pF
Output Capacitance	C_{oss}			480		
Reverse Transfer Capacitance	C_{rss}			435		
Total Gate Charge	Q_g	V_{DS} = - 4 V, V_{GS} = - 4.5 V, I_D = - 5.3 A		19.3	29	nC
		V_{DS} = - 4 V, V_{GS} = - 2.5 V, I_D = - 5.3 A		11.8	18	
Gate-Source Charge	Q_{gs}			1.7		
Gate-Drain Charge	Q_{gd}			6.2		
Gate Resistance	R_g	f = 1 MHz	0.8	4.2	8.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 4 V, R_L = 0.9 Ω I_D = - 4.2 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		20	30	ns
Rise Time	t_r			22	33	
Turn-Off Delay Time	$t_{d(off)}$			46	69	
Fall Time	t_f			20	30	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 2.1	A
Pulse Diode Forward Current[a]	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	I_S = - 4.2 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 4.2 A, dI/dt = 100 A/µs, T_J = 25 °C		40	60	ns
Body Diode Reverse Recovery Charge	Q_{rr}			26	39	nC
Reverse Recovery Fall Time	t_a			17		ns
Reverse Recovery Rise Time	t_b			23		

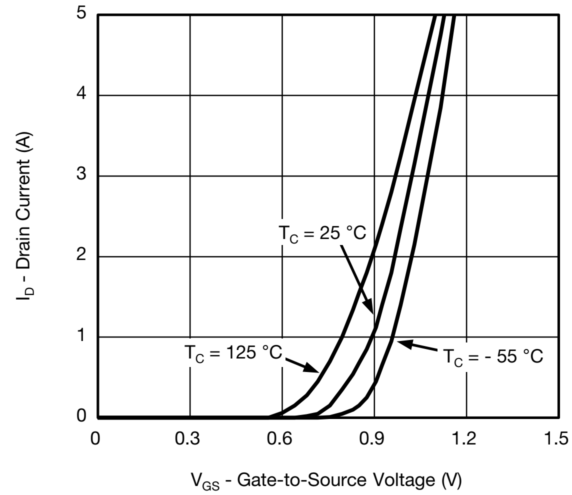
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

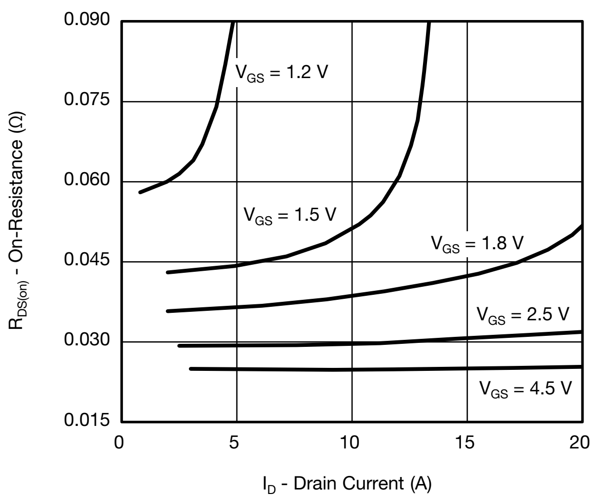
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



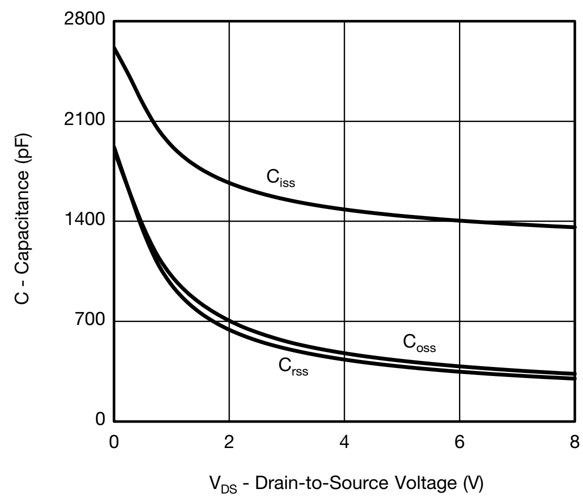
Output Characteristics



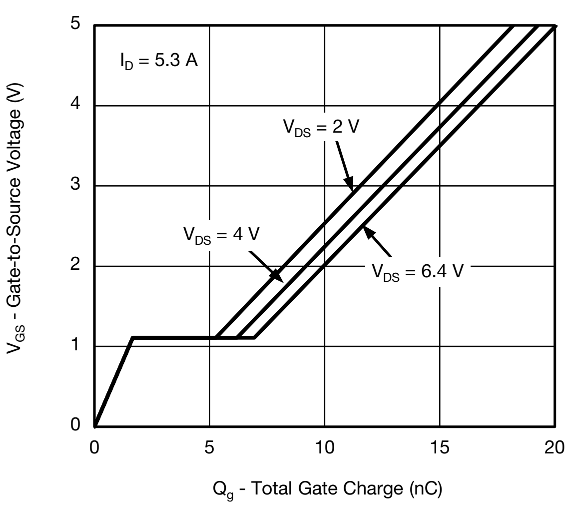
Transfer Characteristics



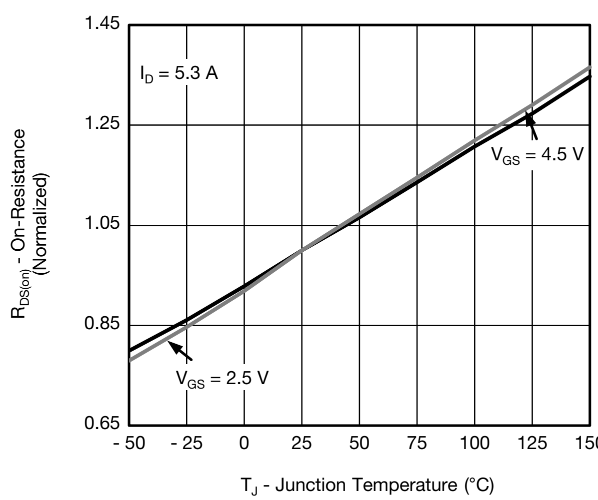
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

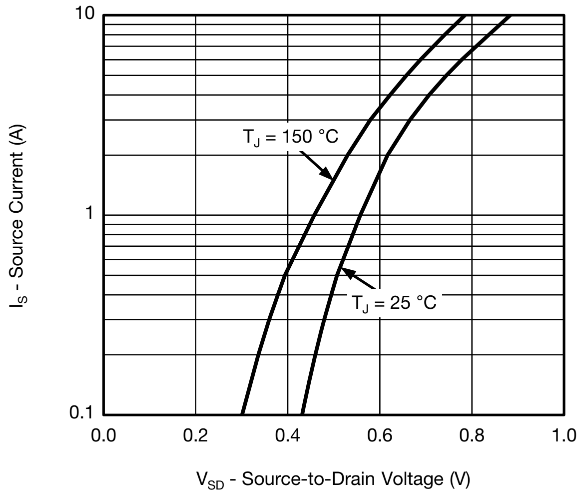


Gate Charge

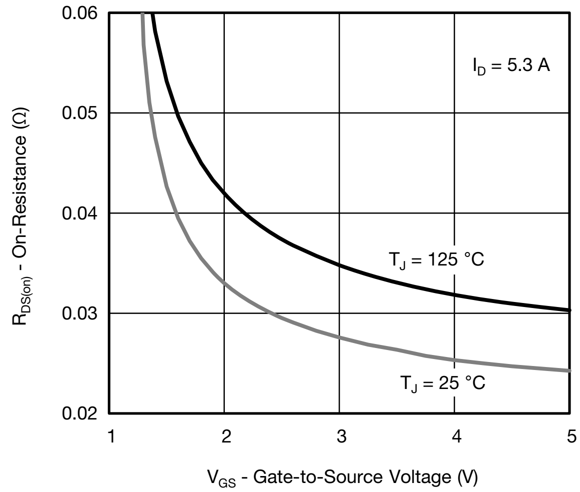


On-Resistance vs. Junction Temperature

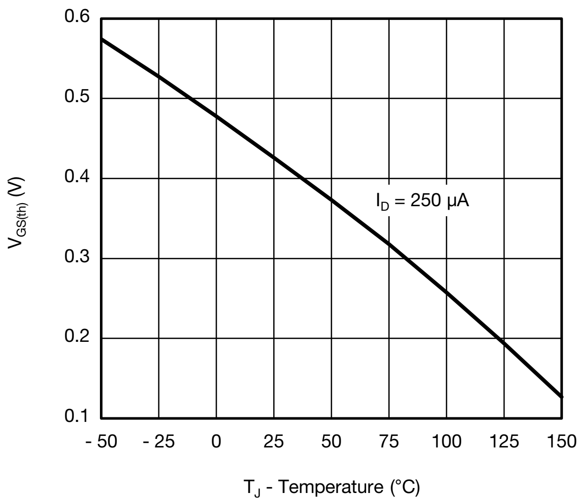
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



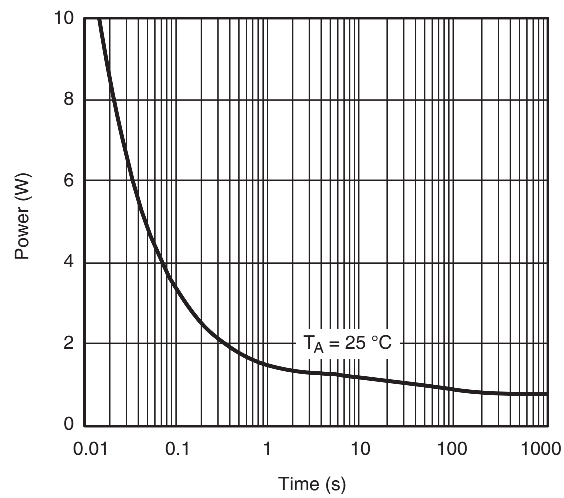
Source-Drain Diode Forward Voltage



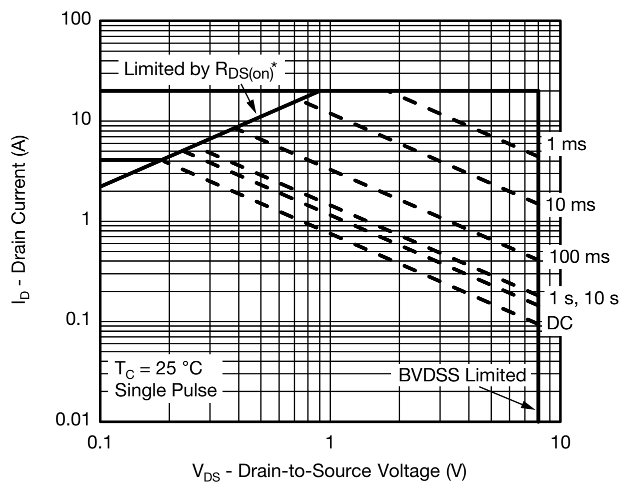
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



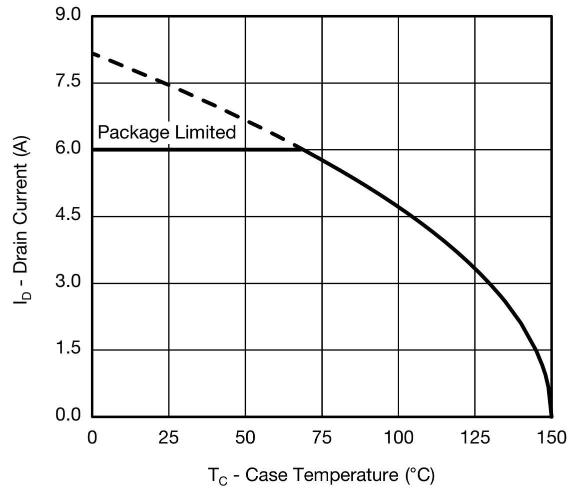
Single Pulse Power



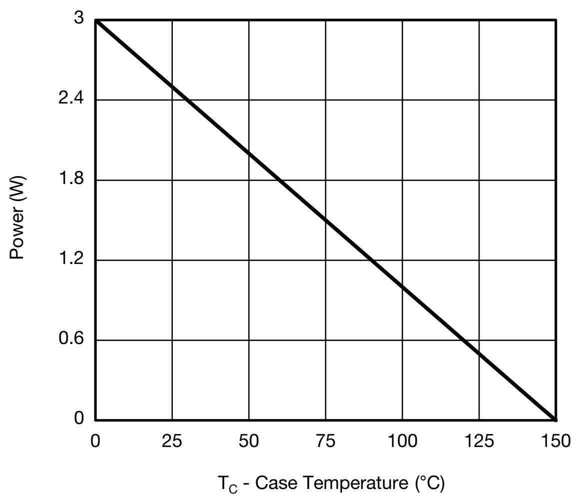
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

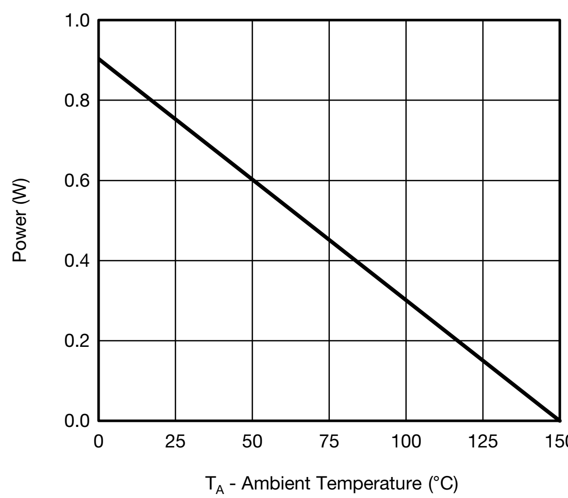
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



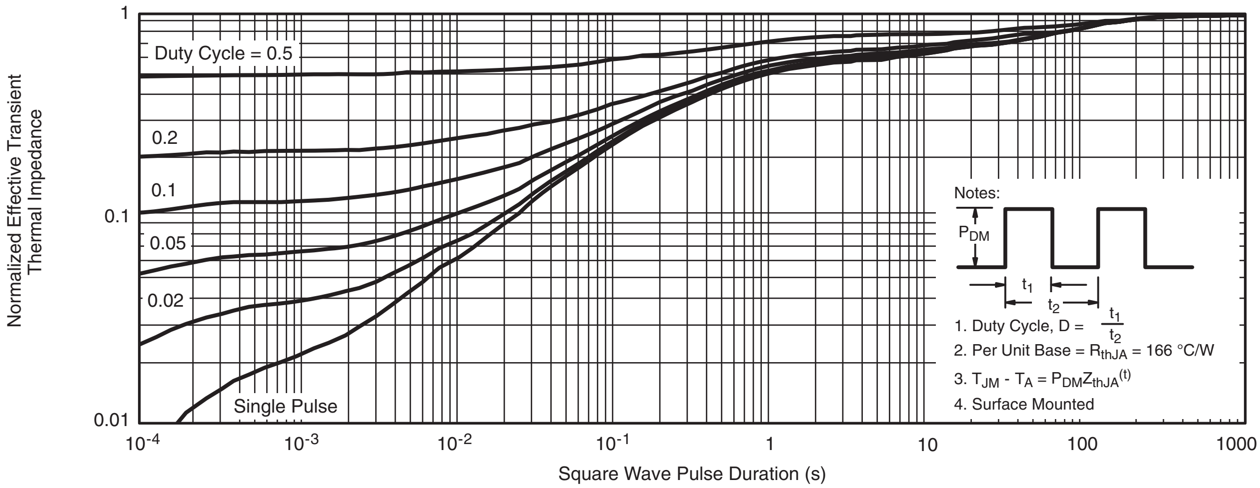
Power, Junction-to-Foot



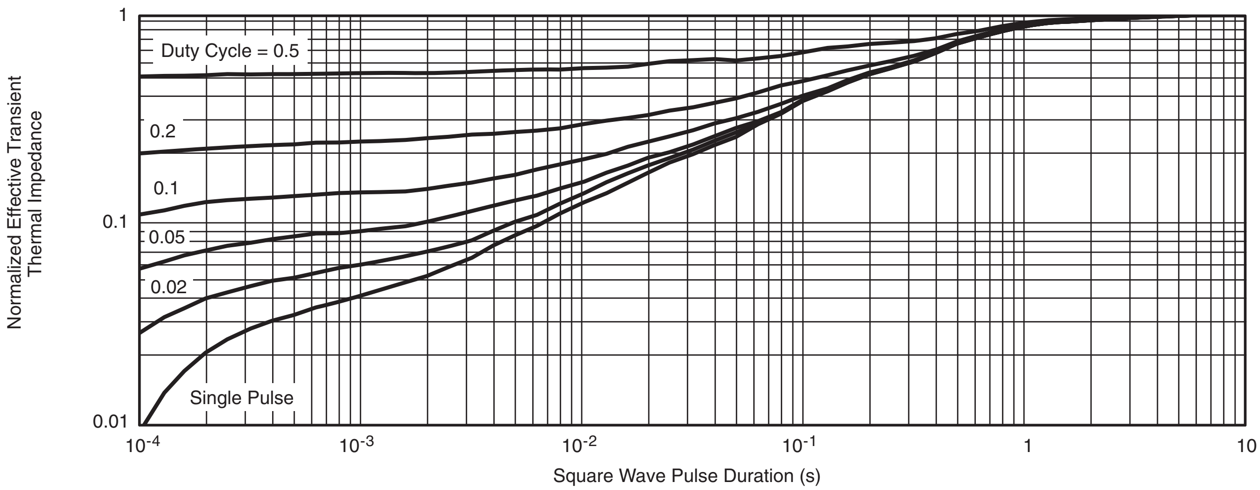
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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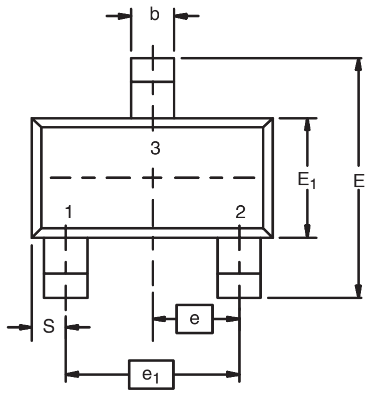
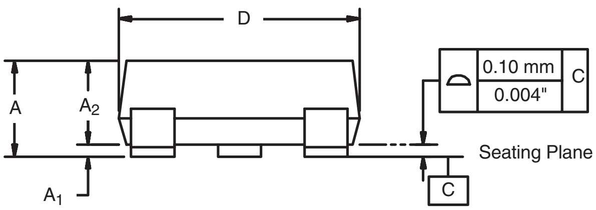
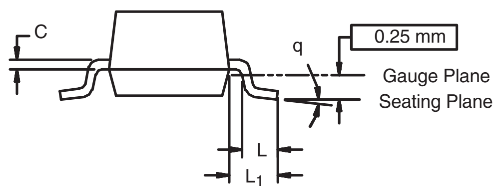
SOT-23 (TO-236): 3-LEAD

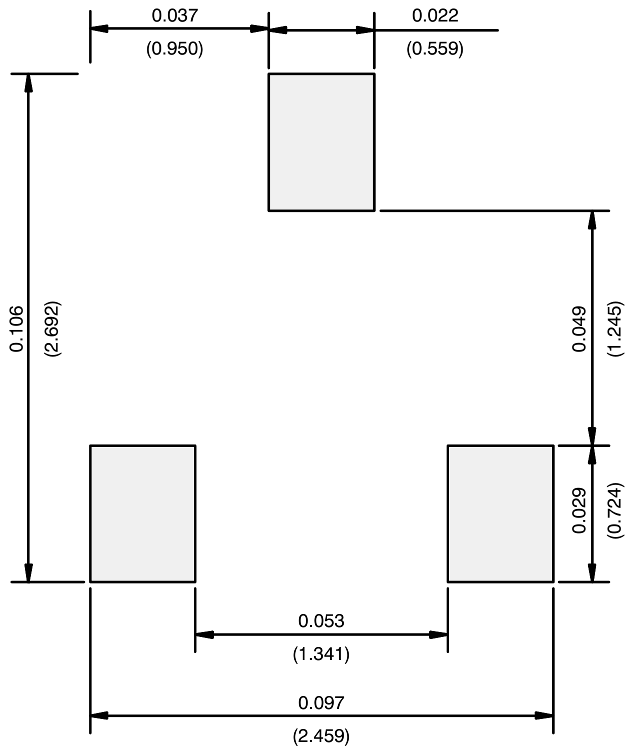






Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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